

**RADIATION HARDENED
 POWER MOSFET
 THRU-HOLE (Low-Ohmic TO-254AA)**

**2N7584T1
 IRHMS67260
 200V, N-CHANNEL
 TECHNOLOGY**

Product Summary

Part Number	Radiation Level	RDS(on)	ID
IRHMS67260	100K Rads (Si)	0.029Ω	45A*
IRHMS63260	300K Rads (Si)	0.029Ω	45A*



International Rectifier's R6™ technology provides superior power MOSFETs for space applications. These devices have improved immunity to Single Event Effect (SEE) and have been characterized for useful performance with Linear Energy Transfer (LET) up to 90MeV/(mg/cm²). Their combination of very low RDS(on) and faster switching times reduces power loss and increases power density in today's high speed switching applications such as DC-DC converters and motor controllers. These devices retain all of the well established advantages of MOSFETs such as voltage control, ease of paralleling and temperature stability of electrical parameters.

Features:

- Low RDS(on)
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Ceramic Eyelets
- Electrically Isolated
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
ID @ VGS = 12V, TC = 25°C	Continuous Drain Current	45*	A
ID @ VGS = 12V, TC = 100°C	Continuous Drain Current	35	
IDM	Pulsed Drain Current ①	180	
PD @ TC = 25°C	Max. Power Dissipation	208	W
	Linear Derating Factor	1.67	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	344	mJ
IAR	Avalanche Current ①	45	A
EAR	Repetitive Avalanche Energy ①	20.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.4	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	9.3 (Typical)	g

* Current is limited by package

For footnotes refer to the last page

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔBV _{DSS} /ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.21	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _D S(on)	Static Drain-to-Source On-State Resistance	—	—	0.029	Ω	V _{GS} = 12V, I _D = 35A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 1.0mA
ΔV _{GS(th)} /ΔT _J	Gate Threshold Voltage Coefficient	—	-11.2	—	mV/°C	
g _{fs}	Forward Transconductance	40	—	—	S	V _{DS} = 25V, I _{DS} = 35A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	V _{DS} = 160V, V _{GS} = 0V
		—	—	25		V _{DS} = 160V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	240	nC	V _{GS} = 12V, I _D = 45A
Q _{gs}	Gate-to-Source Charge	—	—	65		V _{DS} = 100V
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	60		
t _{d(on)}	Turn-On Delay Time	—	—	40	ns	V _{DD} = 100V, I _D = 45A, V _{GS} = 12V, R _G = 2.35Ω
t _r	Rise Time	—	—	60		
t _{d(off)}	Turn-Off Delay Time	—	—	70		
t _f	Fall Time	—	—	30		
L _S + L _D	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm / 0.025 in from package) to Source lead (6mm/ 0.025 in from package)
C _{iss}	Input Capacitance	—	8045	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0MHz
C _{oss}	Output Capacitance	—	953	—		
C _{rss}	Reverse Transfer Capacitance	—	14	—		
R _g	Gate Resistance	—	1.1	—	Ω	f = 1.0MHz, open drain

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	45*	A	
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	180		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _j = 25°C, I _S = 45A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	640	ns	T _j = 25°C, I _F = 45A, di/dt ≤ 100A/μs
Q _{RR}	Reverse Recovery Charge	—	—	10.5	μC	V _{DD} ≤ 25V ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

* Current is limited by package

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	0.60	°C/W	Typical socket mount
R _{thCS}	Case-to-Sink	—	0.21	—		
R _{thJA}	Junction-to-Ambient	—	—	48		

Note: Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

Radiation Characteristics

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International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ T_j = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	Up to 300K Rads (Si)		Units	Test Conditions
		Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	200	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage	2.0	4.0		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100		V _{GS} = -20V
I _{DSS}	Zero Gate Voltage Drain Current	—	10	μA	V _{DS} = 160V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source On-State Resistance (TO-3) ④	—	0.029	Ω	V _{GS} = 12V, I _D = 35A
R _{DS(on)}	Static Drain-to-Source On-State Resistance (Low Ohmic TO-254AA) ④	—	0.029	Ω	V _{GS} = 12V, I _D = 35A
V _{SD}	Diode Forward Voltage ④	—	1.2	V	V _{GS} = 0V, I _D = 45A

1. Part numbers IRHMS67260 and IRHMS63260

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	V _{DS} (V)			
			@V _{GS} = 0V	@V _{GS} = -5V	@V _{GS} = -10V	@V _{GS} = -15V
42 ± 5%	2450 ± 5%	205 ± 5%	200	200	200	190
61 ± 5%	825 ± 5%	66 ± 7.5%	200	200	200	190
90 ± 5%	1470 ± 5%	80 ± 5%	170	170	-	-

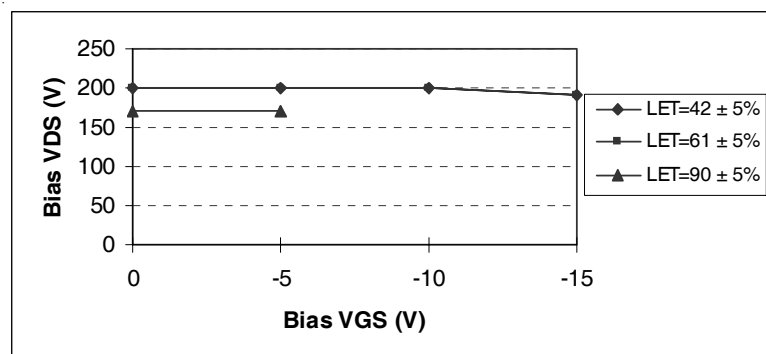


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

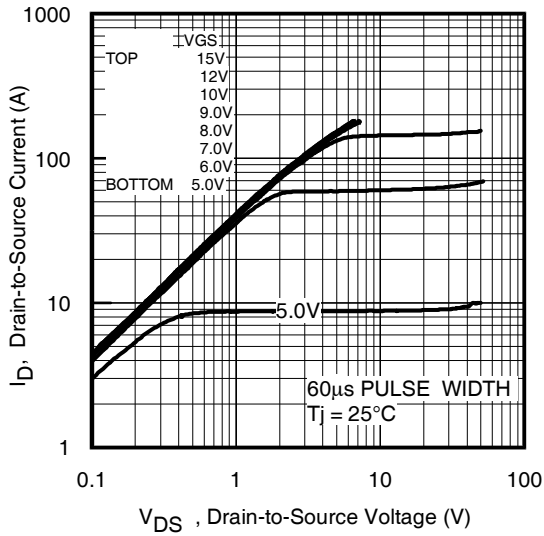


Fig 1. Typical Output Characteristics

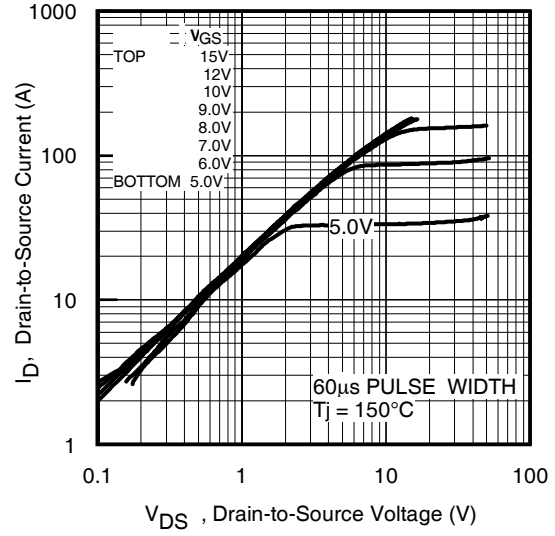


Fig 2. Typical Output Characteristics

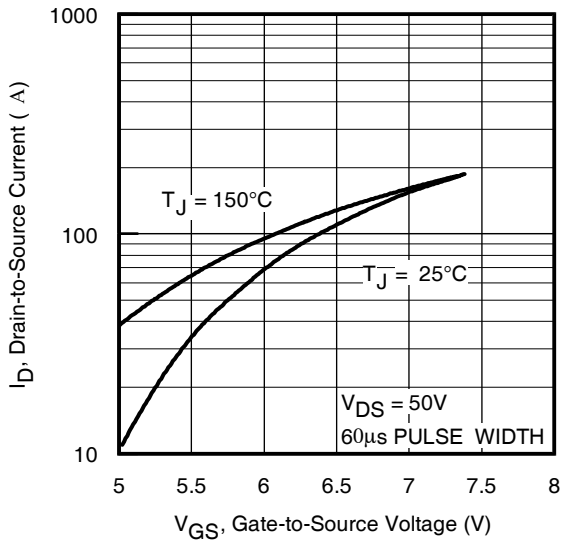


Fig 3. Typical Transfer Characteristics

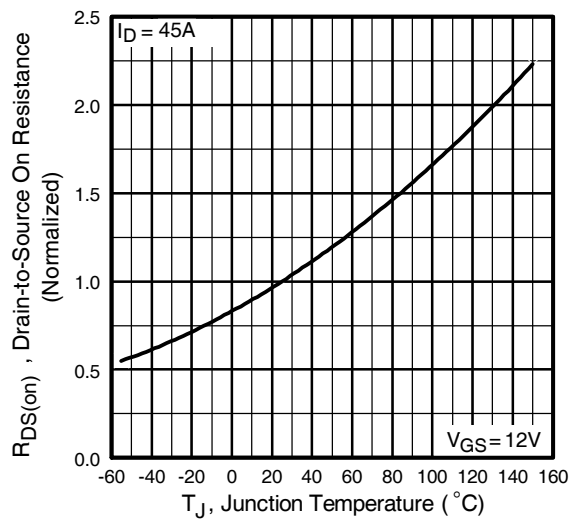


Fig 4. Normalized On-Resistance Vs. Temperature

Pre-Irradiation

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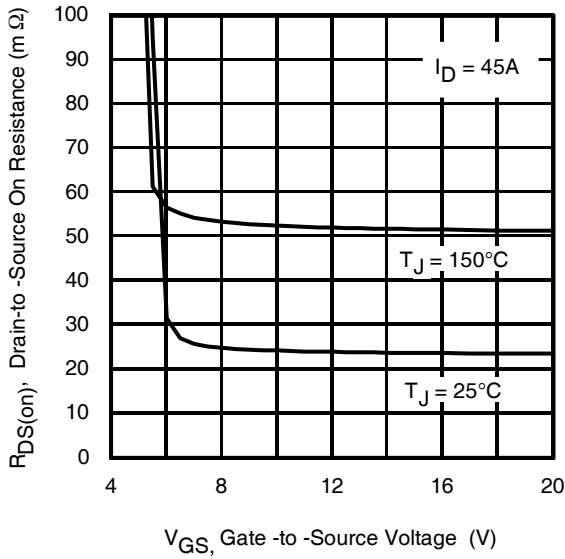


Fig 5. Typical On-Resistance Vs Gate Voltage

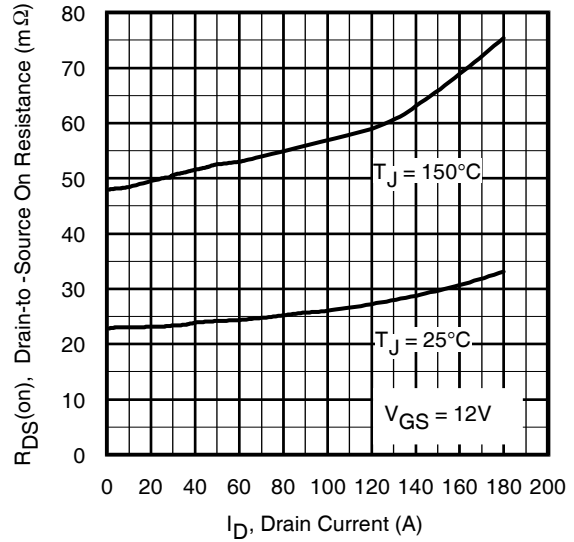


Fig 6. Typical On-Resistance Vs Drain Current

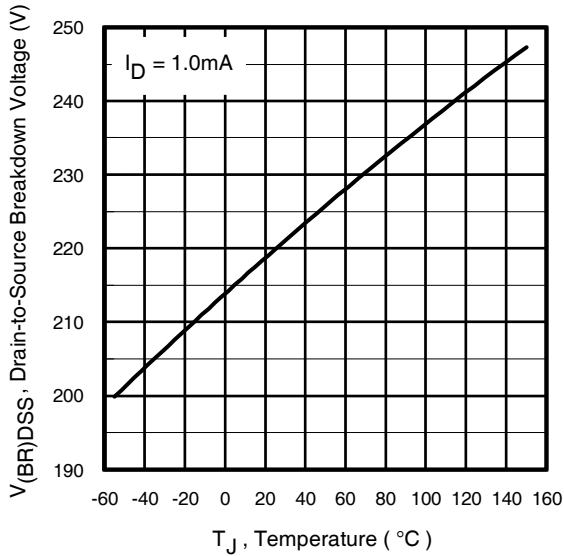


Fig 7. Typical Drain-to-Source Breakdown Voltage Vs Temperature

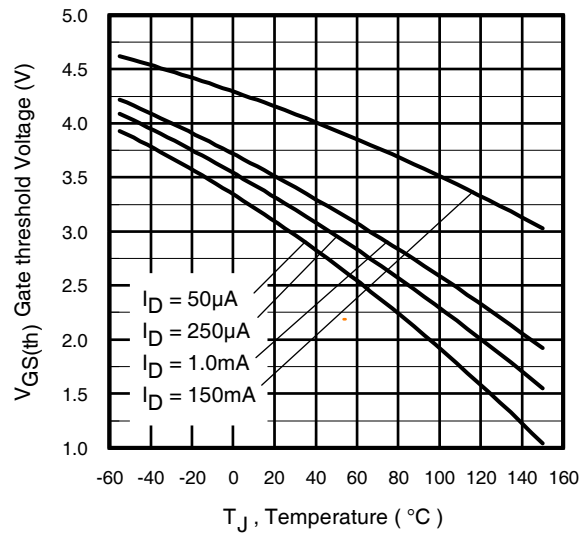


Fig 8. Typical Threshold Voltage Vs Temperature

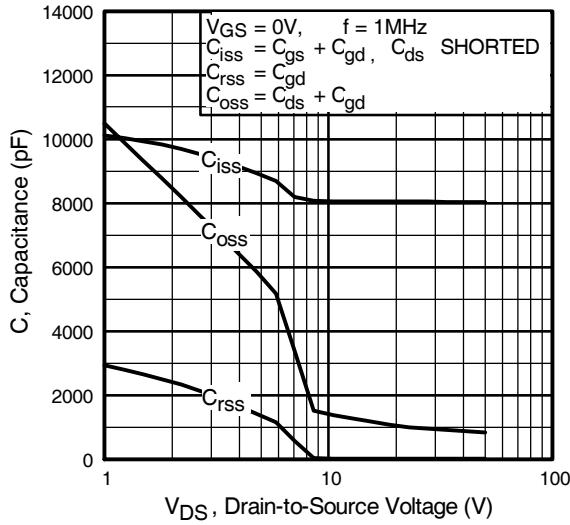


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

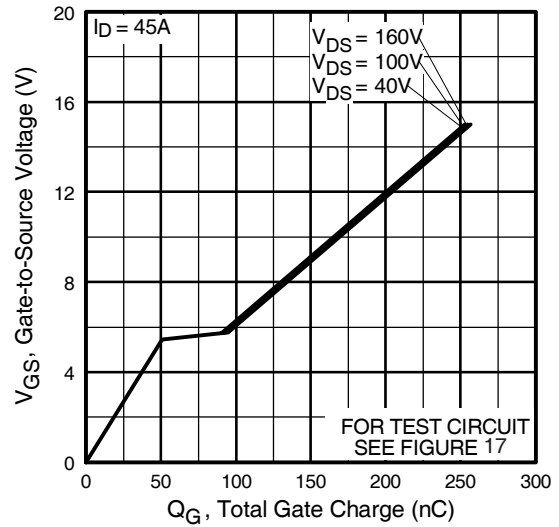


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

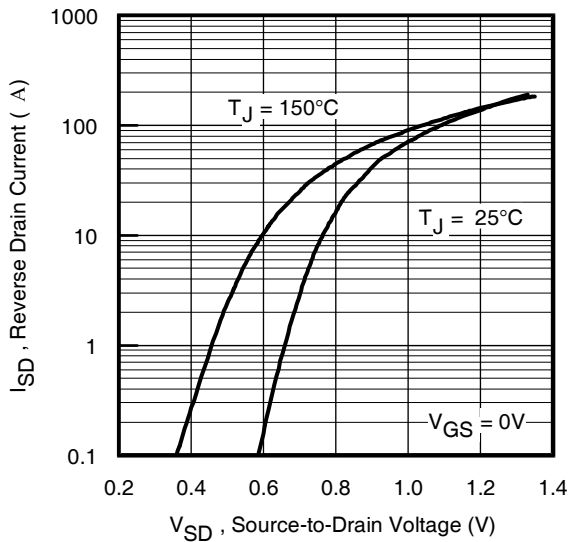


Fig 11. Typical Source-Drain Diode Forward Voltage

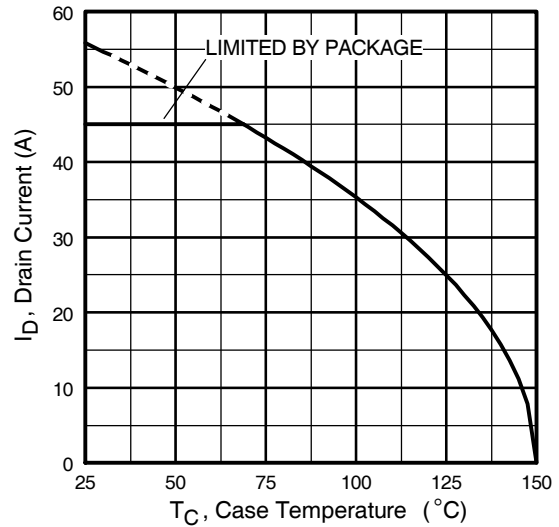


Fig 12. Maximum Drain Current Vs. Case Temperature

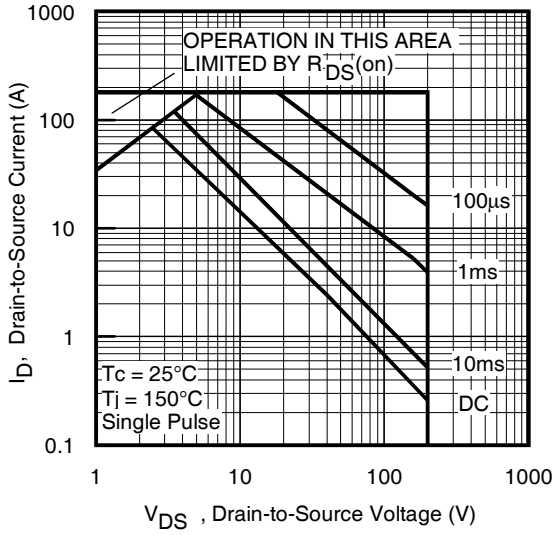


Fig 13. Maximum Safe Operating Area

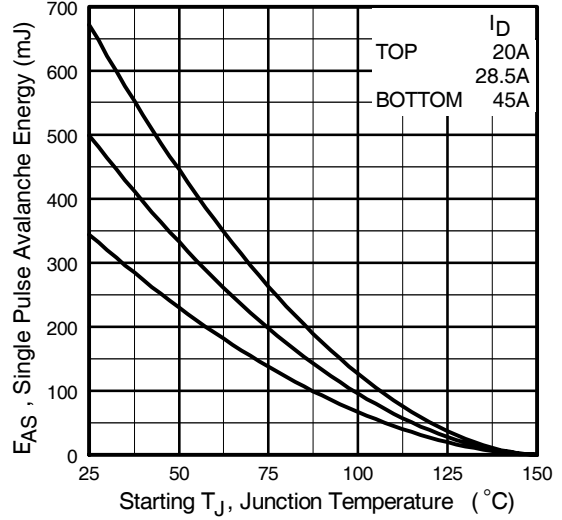


Fig 14. Maximum Avalanche Energy Vs. Drain Current

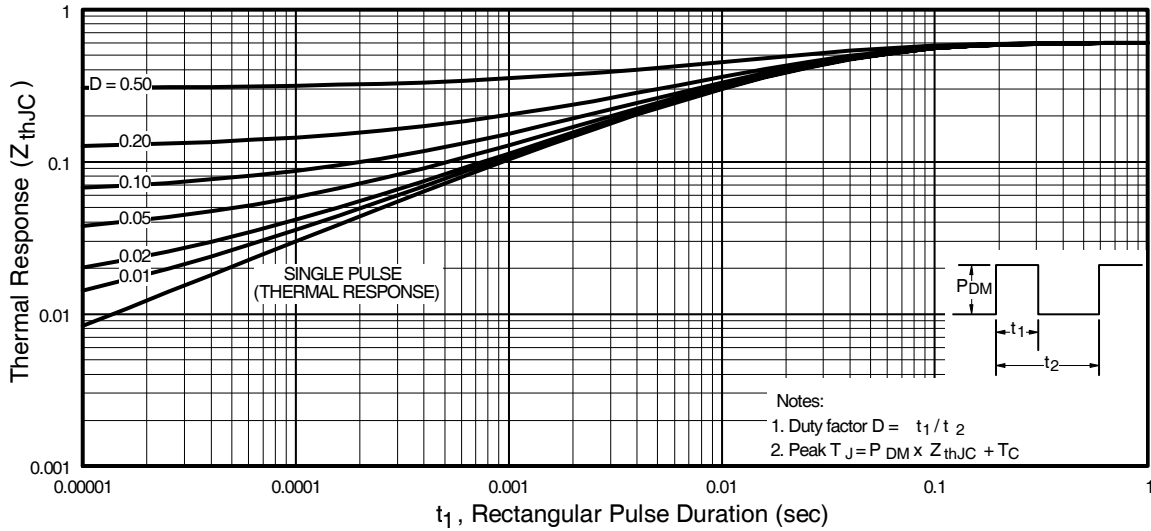


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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Pre-Irradiation

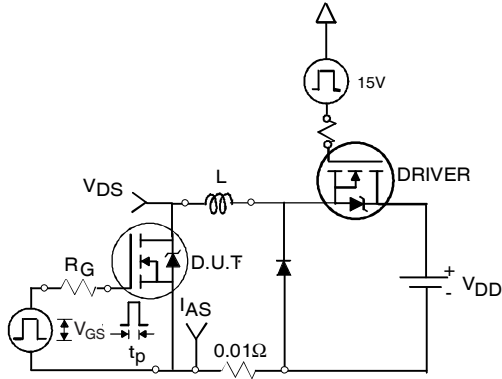


Fig 16a. Unclamped Inductive Test Circuit

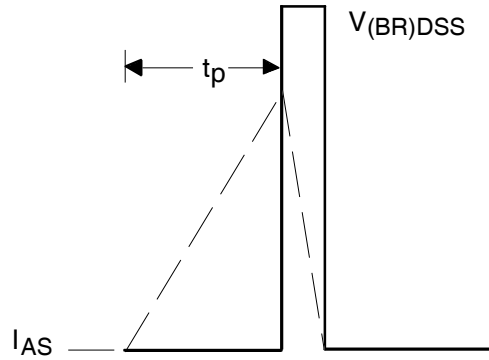


Fig 16b. Unclamped Inductive Waveforms

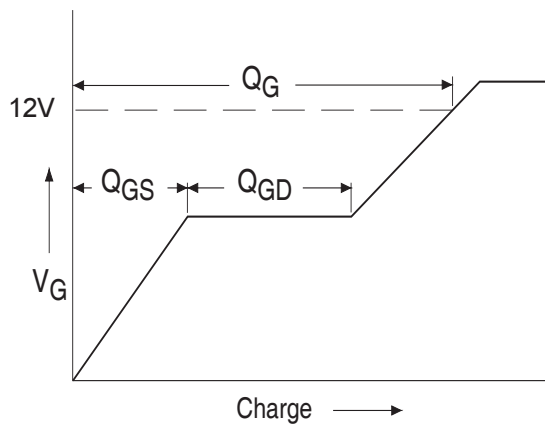


Fig 17a. Basic Gate Charge Waveform

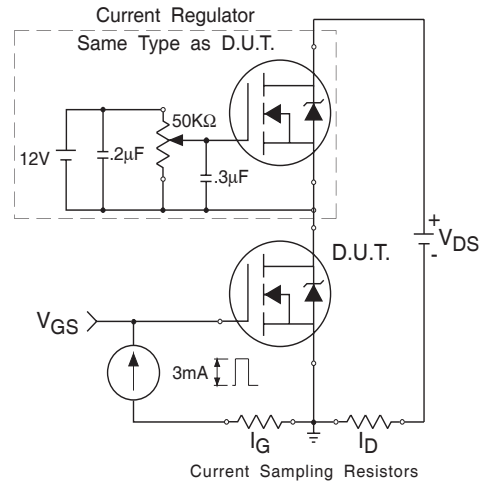


Fig 17b. Gate Charge Test Circuit

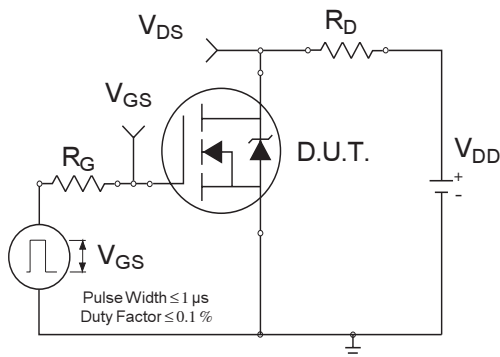


Fig 18a. Switching Time Test Circuit

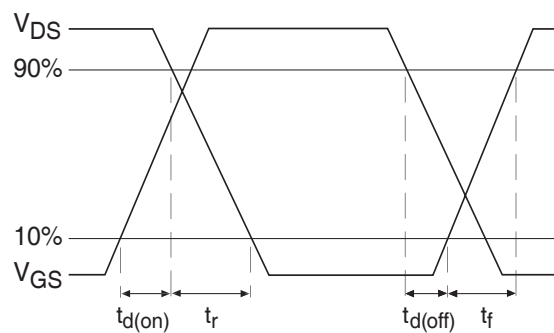


Fig 18b. Switching Time Waveforms

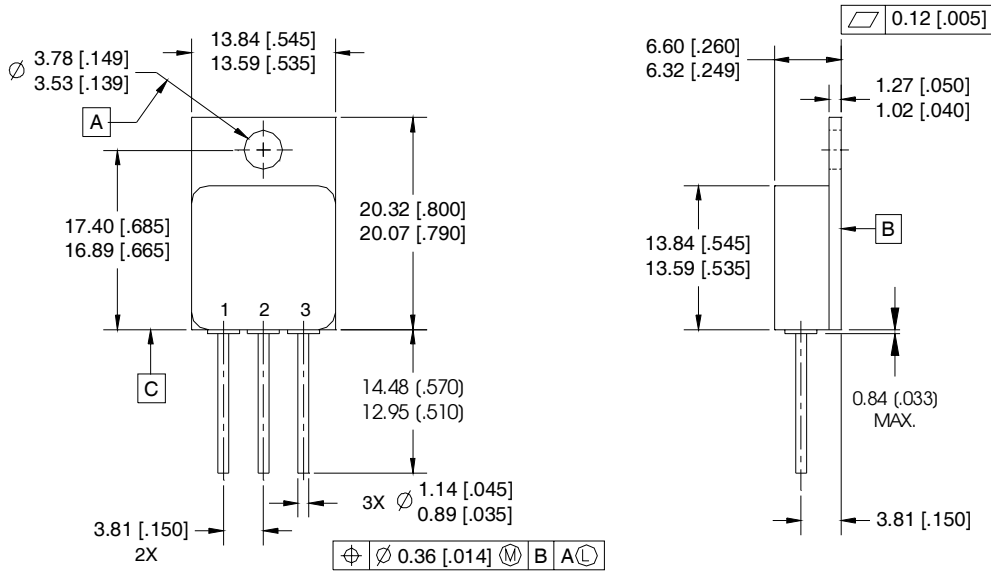
Pre-Irradiation

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Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ C$, $L = 0.34$ mH
Peak $I_L = 45A$, $V_{GS} = 12V$
- ③ $I_{SD} \leq 45A$, $di/dt \leq 840A/\mu s$,
 $V_{DD} \leq 200V$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with V_{DS} Bias.**
160 volt V_{DS} applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions —Low-Ohmic TO-254AA



NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3. CONTROLLING DIMENSION: INCH.
- 4. CONFORMS TO JEDEC OUTLINE TO-254AA.

PIN ASSIGNMENTS

- 1 = DRAIN
- 2 = SOURCE
- 3 = GATE

CAUTION

BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

IR LEOMINSTER : 205 Crawford St., Leominster, Massachusetts 01453, USA Tel: (978) 534-5776

TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.

Data and specifications subject to change without notice. 12/2011